

DESCRIPTION

Mitsubishi 2SA1283 is a silicon PNP epitaxial type transistor designed for relay drive or power supply application.
Complementary with 2SC3243.

FEATURE

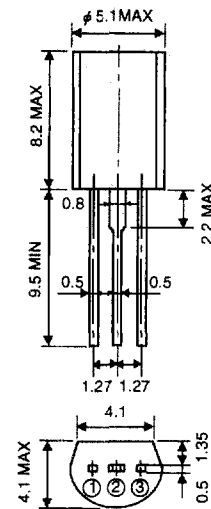
- High voltage $V_{CE0}=-60V$
- High collector current $I_C=-1A$
- Low collector saturation voltage
 $V_{CE(sat)}=-0.11V$ typical (@ $I_C=-500mA, I_B=-25mA$)
- High collector dissipation $P_C=900mW$

APPLICATION

Audio equipment, VCR, relay drive, power supply, etc.

OUTLINE DRAWING

Unit:mm



TERMINAL CONNECTOR

- ① : EMITTER EIAJ : — JEDEC : —
- ② : COLLECTOR EIAJ : — JEDEC : —
- ③ : BASE EIAJ : — JEDEC : —

Note)

The dimension without tolerance represent central value.

MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
V_{CB0}	Collector to Base voltage	-60	V
V_{EB0}	Emitter to Base voltage	-6	V
V_{CE0}	Collector to Emitter voltage	-60	V
I_{CM}	Peak collector current	-2	A
I_C	Collector current	-1	A
P_C	Collector dissipation (Ta=25°C)	900	mW
T_j	Junction temperature	+150	°C
T_{slg}	Storage temperature	-55 to +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CBO}$	C to B break down voltage	$I_C = -10 \mu A, I_E = 0$	-60			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E = -10 \mu A, I_C = 0$	-6			V
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -2 mA, R_{BE} = \infty$	-60			V
I_{CBO}	Collector cut off current	$V_{CB} = -50 V, I_E = 0$			-0.2	μA
I_{EBO}	Emitter cut off current	$V_{EB} = -4V, I_C = 0$			-0.2	μA
$h_{FE} *$	DC forward current gain	$V_{CE} = -4V, I_C = -100mA$	55		300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -500mA, I_B = -25mA$		-0.11	-0.3	V
f_T	Gain band width product	$V_{CE} = -2V, I_E = 10mA$		85		MHz
C_{ob}	Collector output capacitance	$V_{CB} = -10V, I_E = 0, f = 1MHz$		22		pF

* : It shows h_{FE} classification in right table.

Item	C	D	E
h_{FE}	55 to 110	90 to 180	150 to 300

FOR LOW FREQUENCY POWER AMPLIFY APPLICATION
SILICON PNP EPITAXIAL TYPE

TYPICAL CHARACTERISTICS

